



《风光欣》技术资料

2SA1160

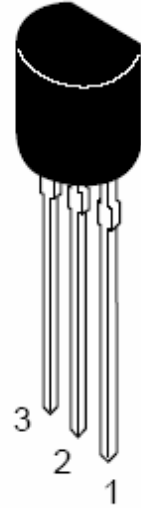
NPN EPITAXIAL SILICON TRANSISTOR

AUDIO FREQUENCY POWER AMPLIFIER

LOW SPEED SWITCHING

TO-92L

ABSOLUTE MAXIMUM RATINGS(TA=25)



1.Base 2.Collector 3.Emitter

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-20	V
Collector-Emitter Voltage	V _{CEO}	-10	V
Emitter -Base Voltage	V _{EBO}	-6	V
Collector Current (DC)	I _c	-2	A
Collector Current (Pulse)	I _{cp}	-4	A
Base Current	I _B	-2	A
Collector Dissipation (T _c =25	P _c	600	mW
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~150	

ELECTRCAL CHARACTERISTICS(TA=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cut-off Current	I _{CB0}	V _{CB} = -20V,I _E =0			-1	μ A
Emitter-Cut-off Current	I _{EBO}	V _{EB} = -6V,I _c =0			-1	μ A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _c = -10A,I _B =0	-10			V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = -1mA,I _c = 0	-6			V
*DC Current Gain	h _{FE1}	V _{CE} = -1V,I _c = -0.5A	140		600	
	h _{FE2}	V _{CE} = -1V,I _c = -4A	60	120		
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = -2A,I _B = -50mA		-0.2	-0.5	V
Base-Emitter Voltage	V _{BE(sat)}	I _c = -1V,I _c = -2A		-0.83	-1.5	V
Current Gain-Bandwidth Product	f _T	V _{CE} = -1V,I _c = -0.5A		140		MHZ
Output Capacitance	C _{OB}	V _{CB} = -10V,I _E =0,f=1MHZ		50		pF

*Pulse Test :PW<350US, Duty Cycle<2%

hFE (1) CLSSIFICAT ION

Classification	A	B	C
HFE(1)	140~200	160~350	300~600